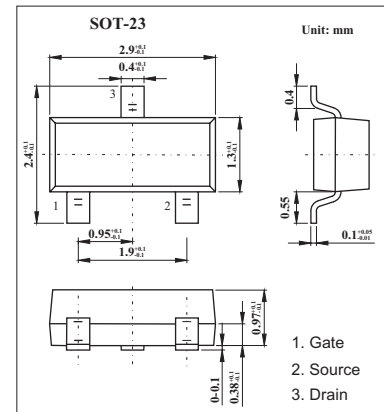
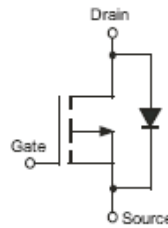


P-Channel Enhancement Mode Field Effect Transistor

KSS84

■ Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Also Available in Lead Free Version

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	-50	V
Drain-Gate Voltage $R_{GS} \leq 20\text{K}\Omega$	V_{DGR}	-50	V
Gate-Source Voltage	V_{GS}	± 20	V
Drain Current *	I_D	-130	mA
Total Power Dissipation *	P_d	300	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_j, T_{STG}	-55 to +150	$^\circ\text{C}$

* Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch;

■ Electrical Characteristics $T_a = 25^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	BV_{DS}	$V_{GS} = 0\text{V}, I_D = -250\mu\text{A}$	-50			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -50\text{V}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$			-15	μA
		$V_{DS} = -50\text{V}, V_{GS} = 0\text{V}, T_J = 125^\circ\text{C}$			-60	μA
		$V_{DS} = -25\text{V}, V_{GS} = 0\text{V}, T_J = 25^\circ\text{C}$			-100	nA
Gate-Body Leakage	I_{GSS}	$V_{GS} = \pm 20\text{V}, V_{DS} = 0\text{V}$			± 10	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -1\text{mA}$	-0.8		-2.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -5\text{V}, I_D = -0.100\text{A}$			10	Ω
Forward Transconductance	g_{FS}	$V_{DS} = -25\text{V}, I_D = -0.1\text{A}$	0.05			S
Input Capacitance	C_{iss}	$V_{DS} = -25\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$			45	pF
Output Capacitance	C_{oss}				25	pF
Reverse Transfer Capacitance	C_{rss}				12	pF
Turn-On Delay Time	$t_{D(ON)}$	$V_{DD} = -30\text{V}, I_D = -0.27\text{A},$		10		ns
Turn-Off Delay Time	$t_{D(OFF)}$	$R_{GEN} = 50\Omega, V_{GS} = -10\text{V}$		18		ns

■ Marking

Marking	K84
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